



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	$75m\Omega @ V_{GS} = -4.5V$	-3.2A
-20V	110m Ω @ V _{GS} = -2.5V	-2.9A

Features

- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMP2110UFDBQ is suitable for automotive applications requiring specific change control; This part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

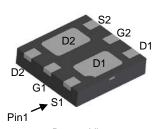
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Power Management Functions
- Portable Power Adaptors

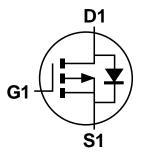
Mechanical Data

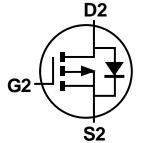
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)



Bottom View





Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UFDBQ-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2110UFDBQ-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

U-DFN2020-6 (Type B)



H6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Ī	Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Ī	Code	0	1	2	3	4	5	6	7	8	9	0	1

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z

DMP2110UFDBQ Document number: DS42661 Rev.2 - 2



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-3.2 -2.6	А
Maximum Continuous Body Diode Forward Current (N	Is	-1.05	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-15	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P _D	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{OJA}	153	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P _D	1.14	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	110	°C/W
Operating and Storage Temperature Range	•	T _{J,} T _{STG}	-55 to +150	°C

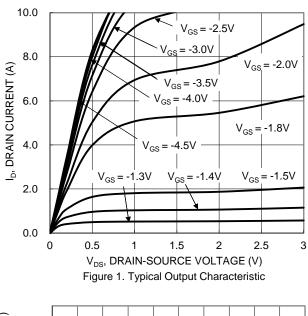
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

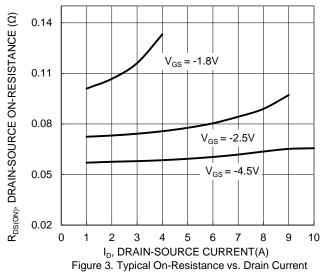
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.45	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		_		75		$V_{GS} = -4.5V, I_D = -2.8A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	110	mΩ	V _{GS} = -2.5V, I _D = -2.0A
		_	_	168		V _{GS} = -1.8V, I _D = -1.0A
Diode Forward Voltage	V_{SD}	_	_	-1.0	V	$V_{GS} = 0V, I_S = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	443		pF	401/1/ 01/
Output Capacitance	Coss	_	59	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	47	_	pF	1 = 1.0lvii iz
Total Gate Charge (V _{GS} = -4.5V)		_	6.0	_	nC	
Total Gate Charge (V _{GS} = -8V)	Q_g	_	12.7	_	nC	451/1 204
Gate-Source Charge	Q _{gs}	_	0.6	_	nC	$V_{DS} = -4.5V, I_{D} = -3.0A$
Gate-Drain Charge	Q _{gd}	_	1.8	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	4.0	_	ns	
Turn-On Rise Time	t _R	_	3.7	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	24.5	_	ns	$R_L = 10\Omega$, $R_g = 6\Omega$
Turn-Off Fall Time	t _F	_	9.5	_	ns]
Body Diode Reverse Recovery Time	t _{RR}	_	8.3	_	ns	I _S = -1.0A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q_{RR}	_	2.0	_	nC	I _S = -1.0A, dI/dt = 100A/μs

5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate. Notes:

7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.







and Gate Voltage

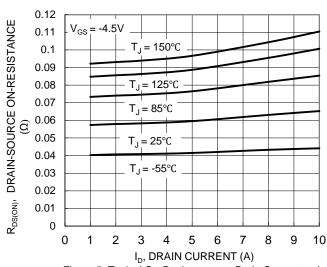
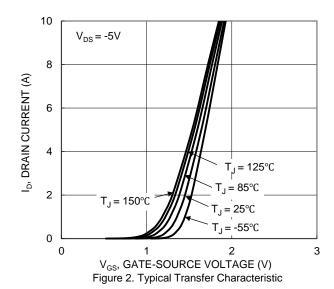
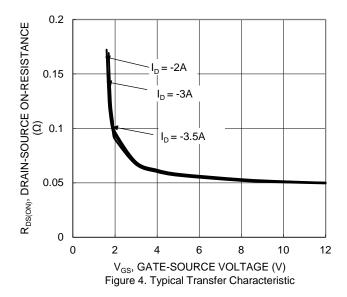


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





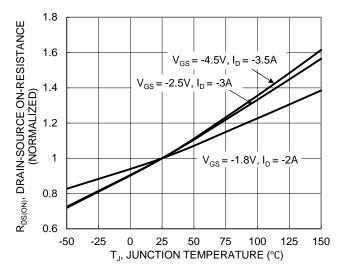


Figure 6. On-Resistance Variation with Junction Temperature



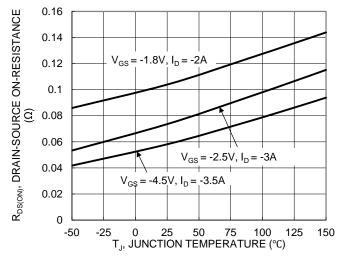
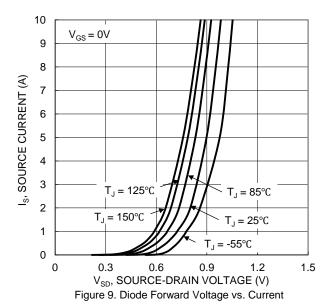
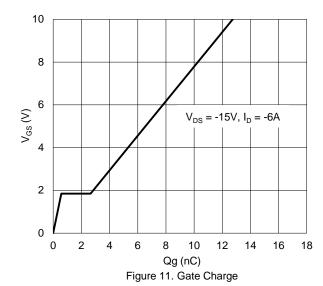


Figure 7. On-Resistance Variation with Junction Temperature





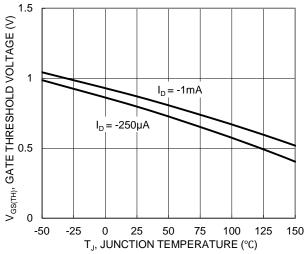
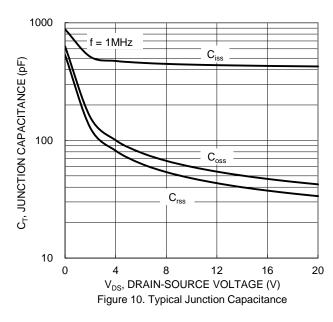
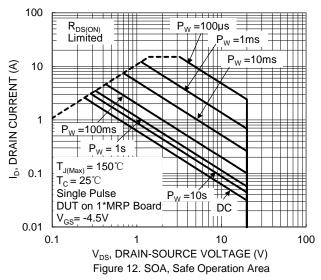


Figure 8. Gate Threshold Variation vs. Junction Temperature







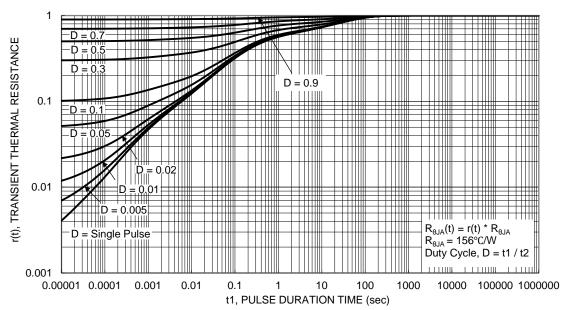
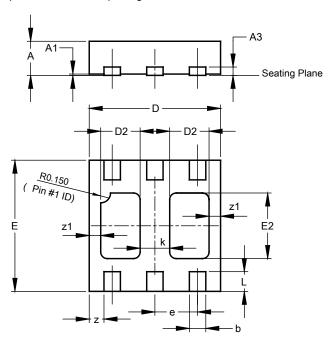


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

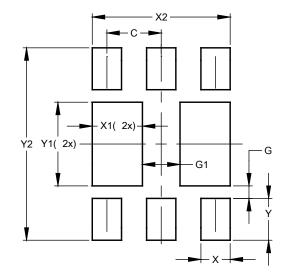
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-6								
	Type B								
Dim	Dim Min Max Ty								
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	2 0.50 0.70		0.60						
е	-	-	0.65						
Е	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
Z	-	-	0.225						
z 1	-	-	0.175						
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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